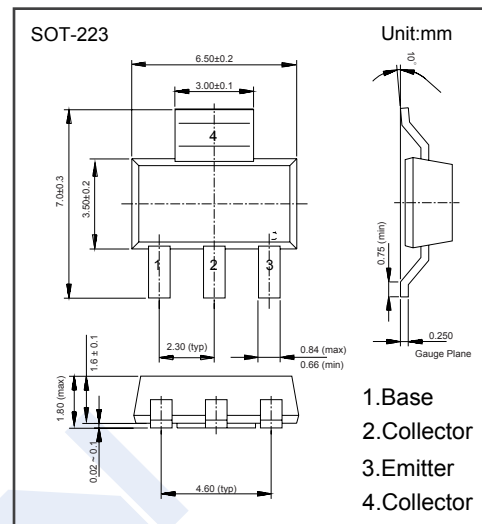


## PNP Transistors

## FZT956 (KZT956)

## ■ Features

- Collector Current Capability  $I_C = -2A$
- Collector Emitter Voltage  $V_{CE0} = -200V$
- Very low saturation voltages
- Excellent gain characteristics specified up to 3 A

■ Absolute Maximum Ratings  $T_a = 25^\circ C$ 

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	$V_{CBO}$	-220	V
Collector - Emitter Voltage	$V_{CEO}$	-200	
Emitter - Base Voltage	$V_{EBO}$	-6	
Collector Current - Continuous	$I_C$	-2	A
Peak Pulse Current	$I_{CM}$	-5	
Collector Power Dissipation	$P_C$	3	W
Junction Temperature	$T_J$	150	$^\circ C$
Storage Temperature range	$T_{stg}$	-55 to 150	

## PNP Transistors

## FZT956 (KZT956)

## ■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V <sub>CB0</sub>	I <sub>C</sub> = -100 μA, I <sub>E</sub> =0	-220			V
Collector- emitter breakdown voltage	V <sub>CER</sub>	I <sub>C</sub> =-1μA, R <sub>B</sub> < 1kΩ	-220			
Collector- emitter breakdown voltage	V <sub>CEO</sub>	I <sub>C</sub> = -10 mA, I <sub>B</sub> =0	-200			
Emitter - base breakdown voltage	V <sub>EBO</sub>	I <sub>E</sub> =-100 μA, I <sub>C</sub> =0	-6			
Collector-base cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> = -200 V, I <sub>E</sub> =0			-50	nA
		V <sub>CB</sub> = -200 V, I <sub>E</sub> =0, Ta = 100°C			-1	μA
Collector cut-off current R < 1kΩ	I <sub>CER</sub>	V <sub>CB</sub> = -200 V, I <sub>E</sub> =0			-50	nA
		V <sub>CB</sub> = -200 V, I <sub>E</sub> =0, Ta = 100°C			-1	μA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> = -6V, I <sub>C</sub> =0			-100	nA
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =-100 mA, I <sub>B</sub> =-10mA			-50	mV
		I <sub>C</sub> =-1 A, I <sub>B</sub> =-100mA			-165	
		I <sub>C</sub> =-2 A, I <sub>B</sub> =-400mA			-275	
Base - emitter saturation voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> =-2 A, I <sub>B</sub> =-400mA			-1110	
Base - emitter turn-on voltage	V <sub>BE(on)</sub>	V <sub>CE</sub> = -5V, I <sub>C</sub> = -2A			-950	
DC current gain	h <sub>FE</sub>	V <sub>CE</sub> = -5V, I <sub>C</sub> = -10mA	100			
		V <sub>CE</sub> =- 5V, I <sub>C</sub> = -1 A	100		300	
		V <sub>CE</sub> = -5V, I <sub>C</sub> = -2 A	50			
		V <sub>CE</sub> = -5V, I <sub>C</sub> = -5 A		10		
Switching Times	t <sub>on</sub>	I <sub>C</sub> =-1A, I <sub>B1</sub> =-100mA I <sub>B2</sub> =100mA, V <sub>CC</sub> =-50V		67		ns
	t <sub>off</sub>			1140		
Collector output capacitance	C <sub>ob</sub>	V <sub>CB</sub> = -20V, f=1MHz		32		pF
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> = -10V, I <sub>C</sub> = -100mA, f=50MHz		110		MHz

Note : Measured under pulsed conditions. Pulse width=300us. Duty cycle ≤2%

## ■ Marking

Marking	FZT956 K****
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### PNP Transistors

### FZT956 (KZT956)

■ Typical Characteristics

